

## Final datasheet

### High speed and low saturation voltage 750 V TRENCHSTOP™ IGBT7 technology co-packed with soft and fast recovery Emitter Controlled 7 diode

#### Features

- $V_{CE} = 750\text{ V}$
- $I_C = 100\text{ A}$
- Low switching losses
- Very low collector-emitter saturation voltage  $V_{CEsat}$
- Very soft, fast recovery antiparallel diode
- Smooth switching behavior
- Humidity robustness
- Optimized for hard switching, two- and three-level topologies
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>

#### Potential applications

- Industrial UPS
- EV Charging
- String inverter
- Energy storage systems (ESS)

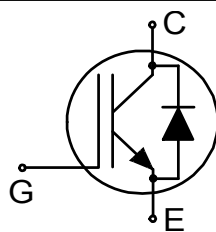
#### Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

#### Description

Package pin definition:

- Pin G – Gate
- Pin C & backside – Collector
- Pin E – Emitter



| Type          | Package        | Marking  |
|---------------|----------------|----------|
| IKWH100N75EH7 | PG-TO247-3-U04 | K100GEH7 |



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## 1 Package

## 1 Package

Table 1 Characteristic values

| Parameter                                                       | Symbol        | Note or test condition                               | Values |      |      | Unit |
|-----------------------------------------------------------------|---------------|------------------------------------------------------|--------|------|------|------|
|                                                                 |               |                                                      | Min.   | Typ. | Max. |      |
| Internal emitter inductance measured 5 mm (0.197 in.) from case | $L_E$         |                                                      |        | 13   |      | nH   |
| Storage temperature                                             | $T_{stg}$     |                                                      | -55    |      | 150  | °C   |
| Soldering temperature                                           | $T_{sold}$    | wave soldering 1.6 mm (0.063 in.) from case for 10 s |        |      | 260  | °C   |
| Mounting torque                                                 | $M$           | M3 screw, Maximum of mounting processes: 3           |        |      | 0.6  | Nm   |
| Thermal resistance, junction-ambient                            | $R_{th(j-a)}$ |                                                      |        |      | 40   | K/W  |
| IGBT thermal resistance, junction-case                          | $R_{th(j-c)}$ |                                                      |        | 0.27 | 0.35 | K/W  |
| Diode thermal resistance, junction-case                         | $R_{th(j-c)}$ |                                                      |        | 0.36 | 0.47 | K/W  |

## 2 IGBT

Table 2 Maximum rated values

| Parameter                                              | Symbol       | Note or test condition                                                                     |                       | Values   | Unit |
|--------------------------------------------------------|--------------|--------------------------------------------------------------------------------------------|-----------------------|----------|------|
| Collector-emitter voltage                              | $V_{CE}$     | $T_{vj} \geq 25\text{ °C}$                                                                 |                       | 750      | V    |
| DC collector current, limited by $T_{vjmax}$           | $I_C$        | limited by bondwire                                                                        | $T_c = 25\text{ °C}$  | 140      | A    |
|                                                        |              |                                                                                            | $T_c = 100\text{ °C}$ | 122      |      |
| Pulsed collector current, $t_p$ limited by $T_{vjmax}$ | $I_{Cpulse}$ |                                                                                            |                       | 400      | A    |
| Turn-off safe operating area                           |              | $V_{CE} \leq 750\text{ V}$ , $t_p \leq 1\text{ }\mu\text{s}$ , $T_{vj} \leq 175\text{ °C}$ |                       | 400      | A    |
| Gate-emitter voltage                                   | $V_{GE}$     |                                                                                            |                       | $\pm 20$ | V    |
| Transient gate-emitter voltage                         | $V_{GE}$     | $t_p \leq 10\text{ }\mu\text{s}$ , $D < 0.01$                                              |                       | $\pm 30$ | V    |
| Power dissipation                                      | $P_{tot}$    |                                                                                            | $T_c = 25\text{ °C}$  | 429      | W    |
|                                                        |              |                                                                                            | $T_c = 100\text{ °C}$ | 214      |      |

Table 3 Characteristic values

| Parameter                            | Symbol       | Note or test condition                                                                                                      |                                                    | Values |      |      | Unit          |
|--------------------------------------|--------------|-----------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------|--------|------|------|---------------|
|                                      |              |                                                                                                                             |                                                    | Min.   | Typ. | Max. |               |
| Collector-emitter saturation voltage | $V_{CEsat}$  | $I_C = 100\text{ A}$ , $V_{GE} = 15\text{ V}$                                                                               | $T_{vj} = 25\text{ °C}$                            |        | 1.45 | 1.75 | V             |
|                                      |              |                                                                                                                             | $T_{vj} = 175\text{ °C}$                           |        | 1.75 |      |               |
| Gate-emitter threshold voltage       | $V_{GETh}$   | $I_C = 0.88\text{ mA}$ , $V_{CE} = V_{GE}$                                                                                  |                                                    | 3.2    | 4    | 4.8  | V             |
| Zero gate-voltage collector current  | $I_{CES}$    | $V_{CE} = 750\text{ V}$ , $V_{GE} = 0\text{ V}$                                                                             | $T_{vj} = 25\text{ °C}$                            |        |      | 30   | $\mu\text{A}$ |
|                                      |              |                                                                                                                             | $T_{vj} = 175\text{ °C}$                           |        | 3000 |      |               |
| Gate-emitter leakage current         | $I_{GES}$    | $V_{CE} = 0\text{ V}$ , $V_{GE} = 20\text{ V}$                                                                              |                                                    |        |      | 100  | nA            |
| Transconductance                     | $g_{fs}$     | $I_C = 100\text{ A}$ , $V_{CE} = 20\text{ V}$                                                                               |                                                    |        | 115  |      | S             |
| Input capacitance                    | $C_{ies}$    | $V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 100\text{ kHz}$                                                       |                                                    |        | 5160 |      | pF            |
| Output capacitance                   | $C_{oes}$    | $V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 100\text{ kHz}$                                                       |                                                    |        | 148  |      | pF            |
| Reverse transfer capacitance         | $C_{res}$    | $V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 100\text{ kHz}$                                                       |                                                    |        | 19   |      | pF            |
| Gate charge                          | $Q_G$        | $V_{CC} = 600\text{ V}$ , $I_C = 100\text{ A}$ , $V_{GE} = 15\text{ V}$                                                     |                                                    |        | 205  |      | nC            |
| Turn-on delay time                   | $t_{d(on)}$  | $V_{CC} = 400\text{ V}$ , $V_{GE} = 0/15\text{ V}$ ,<br>$R_{G(on)} = 10\text{ }\Omega$ ,<br>$R_{G(off)} = 10\text{ }\Omega$ | $T_{vj} = 25\text{ °C}$ ,<br>$I_C = 100\text{ A}$  |        | 31   |      | ns            |
|                                      |              |                                                                                                                             | $T_{vj} = 175\text{ °C}$ ,<br>$I_C = 100\text{ A}$ |        | 30   |      |               |
| Rise time (inductive load)           | $t_r$        | $V_{CC} = 400\text{ V}$ , $V_{GE} = 0/15\text{ V}$ ,<br>$R_{G(on)} = 10\text{ }\Omega$ ,<br>$R_{G(off)} = 10\text{ }\Omega$ | $T_{vj} = 25\text{ °C}$ ,<br>$I_C = 100\text{ A}$  |        | 39   |      | ns            |
|                                      |              |                                                                                                                             | $T_{vj} = 175\text{ °C}$ ,<br>$I_C = 100\text{ A}$ |        | 41   |      |               |
| Turn-off delay time                  | $t_{d(off)}$ | $V_{CC} = 400\text{ V}$ , $V_{GE} = 0/15\text{ V}$ ,<br>$R_{G(on)} = 10\text{ }\Omega$ ,<br>$R_{G(off)} = 10\text{ }\Omega$ | $T_{vj} = 25\text{ °C}$ ,<br>$I_C = 100\text{ A}$  |        | 237  |      | ns            |
|                                      |              |                                                                                                                             | $T_{vj} = 175\text{ °C}$ ,<br>$I_C = 100\text{ A}$ |        | 266  |      |               |
| Fall time (inductive load)           | $t_f$        | $V_{CC} = 400\text{ V}$ , $V_{GE} = 0/15\text{ V}$ ,<br>$R_{G(on)} = 10\text{ }\Omega$ ,<br>$R_{G(off)} = 10\text{ }\Omega$ | $T_{vj} = 25\text{ °C}$ ,<br>$I_C = 100\text{ A}$  |        | 48   |      | ns            |
|                                      |              |                                                                                                                             | $T_{vj} = 175\text{ °C}$ ,<br>$I_C = 100\text{ A}$ |        | 55   |      |               |
| Turn-on energy                       | $E_{on}$     | $V_{CC} = 400\text{ V}$ , $V_{GE} = 0/15\text{ V}$ ,<br>$R_{G(on)} = 10\text{ }\Omega$ ,<br>$R_{G(off)} = 10\text{ }\Omega$ | $T_{vj} = 25\text{ °C}$ ,<br>$I_C = 100\text{ A}$  |        | 3.2  |      | mJ            |
|                                      |              |                                                                                                                             | $T_{vj} = 175\text{ °C}$ ,<br>$I_C = 100\text{ A}$ |        | 3.9  |      |               |

(table continues...)

**Table 3** (continued) Characteristic values

| Parameter                      | Symbol    | Note or test condition                                                                                          | Values                                             |      |      | Unit |
|--------------------------------|-----------|-----------------------------------------------------------------------------------------------------------------|----------------------------------------------------|------|------|------|
|                                |           |                                                                                                                 | Min.                                               | Typ. | Max. |      |
| Turn-off energy                | $E_{off}$ | $V_{CC} = 400\text{ V}$ , $V_{GE} = 0/15\text{ V}$ ,<br>$R_{G(on)} = 10\ \Omega$ ,<br>$R_{G(off)} = 10\ \Omega$ | $T_{vj} = 25\text{ °C}$ ,<br>$I_C = 100\text{ A}$  | 1.8  |      | mJ   |
|                                |           |                                                                                                                 | $T_{vj} = 175\text{ °C}$ ,<br>$I_C = 100\text{ A}$ | 2.6  |      |      |
| Total switching energy         | $E_{ts}$  | $V_{CC} = 400\text{ V}$ , $V_{GE} = 0/15\text{ V}$ ,<br>$R_{G(on)} = 10\ \Omega$ ,<br>$R_{G(off)} = 10\ \Omega$ | $T_{vj} = 25\text{ °C}$ ,<br>$I_C = 100\text{ A}$  | 5    |      | mJ   |
|                                |           |                                                                                                                 | $T_{vj} = 175\text{ °C}$ ,<br>$I_C = 100\text{ A}$ | 6.5  |      |      |
| Operating junction temperature | $T_{vj}$  |                                                                                                                 | -40                                                |      | 175  | °C   |

### 3 Diode

**Table 4** Maximum rated values

| Parameter                                          | Symbol       | Note or test condition |                       | Values | Unit |
|----------------------------------------------------|--------------|------------------------|-----------------------|--------|------|
| Diode forward current, limited by $T_{vjmax}$      | $I_F$        | limited by bondwire    | $T_c = 25\text{ °C}$  | 140    | A    |
|                                                    |              |                        | $T_c = 100\text{ °C}$ | 104    |      |
| Diode pulsed current, $t_p$ limited by $T_{vjmax}$ | $I_{Fpulse}$ |                        |                       | 400    | A    |
| Power dissipation                                  | $P_{tot}$    |                        | $T_c = 25\text{ °C}$  | 319    | W    |
|                                                    |              |                        | $T_c = 100\text{ °C}$ | 160    |      |

**Table 5** Characteristic values

| Parameter                     | Symbol   | Note or test condition                          | Values                                             |      |      | Unit          |
|-------------------------------|----------|-------------------------------------------------|----------------------------------------------------|------|------|---------------|
|                               |          |                                                 | Min.                                               | Typ. | Max. |               |
| Diode forward voltage         | $V_F$    | $I_F = 100\text{ A}$                            | $T_{vj} = 25\text{ °C}$                            | 1.65 | 2    | V             |
|                               |          |                                                 | $T_{vj} = 175\text{ °C}$                           | 1.6  |      |               |
| Diode reverse recovery time   | $t_{rr}$ | $V_R = 400\text{ V}$ , $R_{G(on)} = 10\ \Omega$ | $T_{vj} = 25\text{ °C}$ ,<br>$I_F = 100\text{ A}$  | 105  |      | ns            |
|                               |          |                                                 | $T_{vj} = 175\text{ °C}$ ,<br>$I_F = 100\text{ A}$ | 153  |      |               |
| Diode reverse recovery charge | $Q_{rr}$ | $V_R = 400\text{ V}$ , $R_{G(on)} = 10\ \Omega$ | $T_{vj} = 25\text{ °C}$ ,<br>$I_F = 100\text{ A}$  | 2.7  |      | $\mu\text{C}$ |
|                               |          |                                                 | $T_{vj} = 175\text{ °C}$ ,<br>$I_F = 100\text{ A}$ | 5.5  |      |               |

(table continues...)

Table 5 (continued) Characteristic values

| Parameter                                           | Symbol       | Note or test condition                       | Values                                            |      |      | Unit             |
|-----------------------------------------------------|--------------|----------------------------------------------|---------------------------------------------------|------|------|------------------|
|                                                     |              |                                              | Min.                                              | Typ. | Max. |                  |
| Diode peak reverse recovery current                 | $I_{rrm}$    | $V_R = 400 \text{ V}, R_{G(on)} = 10 \Omega$ | $T_{vj} = 25^\circ\text{C}, I_F = 100 \text{ A}$  | 42.3 |      | A                |
|                                                     |              |                                              | $T_{vj} = 175^\circ\text{C}, I_F = 100 \text{ A}$ | 59   |      |                  |
| Diode peak rate of fall of reverse recovery current | $di_{rr}/dt$ | $V_R = 400 \text{ V}, R_{G(on)} = 10 \Omega$ | $T_{vj} = 25^\circ\text{C}, I_F = 100 \text{ A}$  | -665 |      | A/ $\mu\text{s}$ |
|                                                     |              |                                              | $T_{vj} = 175^\circ\text{C}, I_F = 100 \text{ A}$ | -670 |      |                  |
| Reverse recovery energy                             | $E_{rec}$    | $V_R = 400 \text{ V}, R_{G(on)} = 10 \Omega$ | $T_{vj} = 25^\circ\text{C}, I_F = 100 \text{ A}$  | 0.55 |      | mJ               |
|                                                     |              |                                              | $T_{vj} = 175^\circ\text{C}, I_F = 100 \text{ A}$ | 1.33 |      |                  |
| Operating junction temperature                      | $T_{vj}$     |                                              | -40                                               |      | 175  | $^\circ\text{C}$ |

**Note:** For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Electrical Characteristic at  $T_{vj} = 25^\circ\text{C}$ , unless otherwise specified.

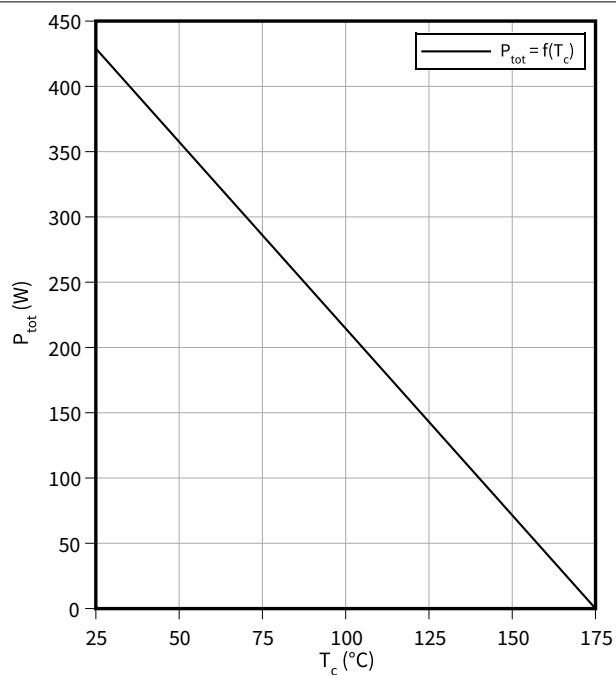
Dynamic test circuit, parasitic inductance  $L_\sigma = 8 \text{ nH}$ , parasitic capacitor  $C_\sigma = 30 \text{ pF}$  from Fig. E. Energy losses include "tail" and diode reverse recovery.

## 4 Characteristics diagrams

### Power dissipation as a function of case temperature

$$P_{\text{tot}} = f(T_c)$$

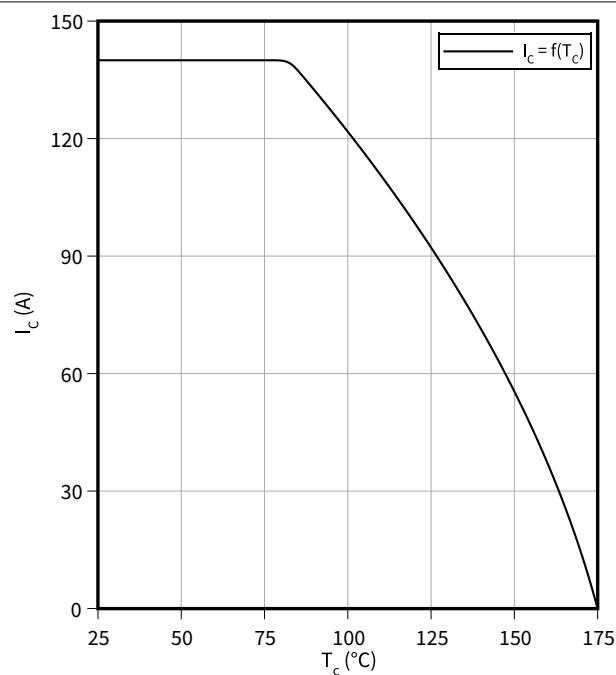
$$T_{vj} \leq 175\text{ °C}$$



### Collector current as a function of case temperature

$$I_C = f(T_c)$$

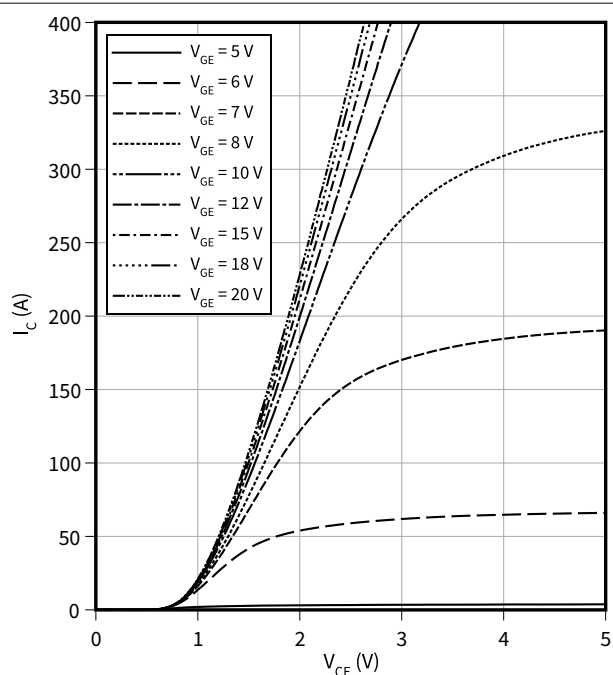
$$T_{vj} \leq 175\text{ °C}, V_{GE} \geq 15\text{ V}$$



### Typical output characteristic

$$I_C = f(V_{CE})$$

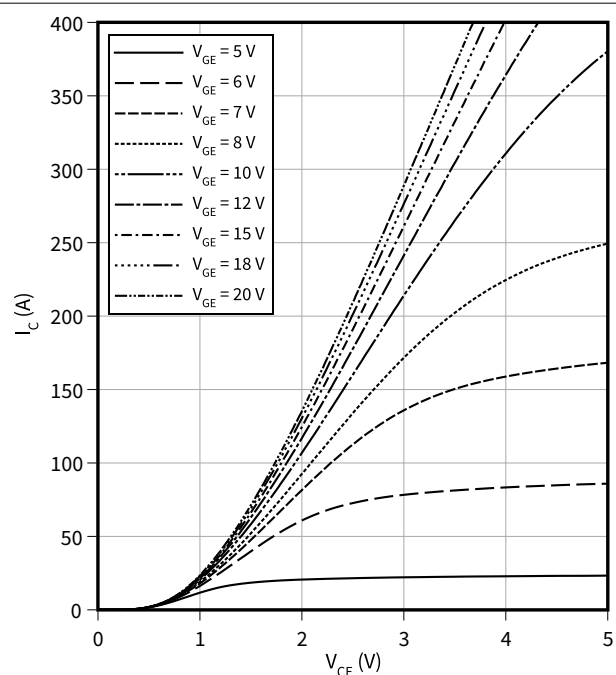
$$T_{vj} = 25\text{ °C}$$



### Typical output characteristic

$$I_C = f(V_{CE})$$

$$T_{vj} = 175\text{ °C}$$

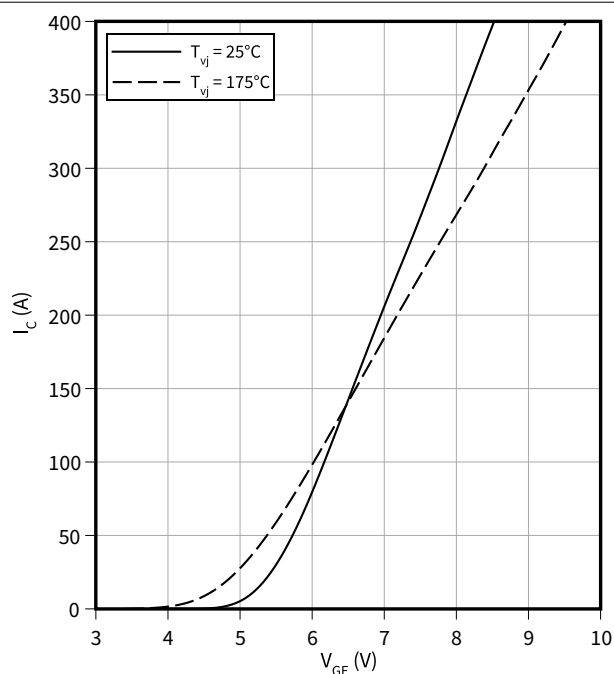


## 4 Characteristics diagrams

## Typical transfer characteristic

$$I_C = f(V_{GE})$$

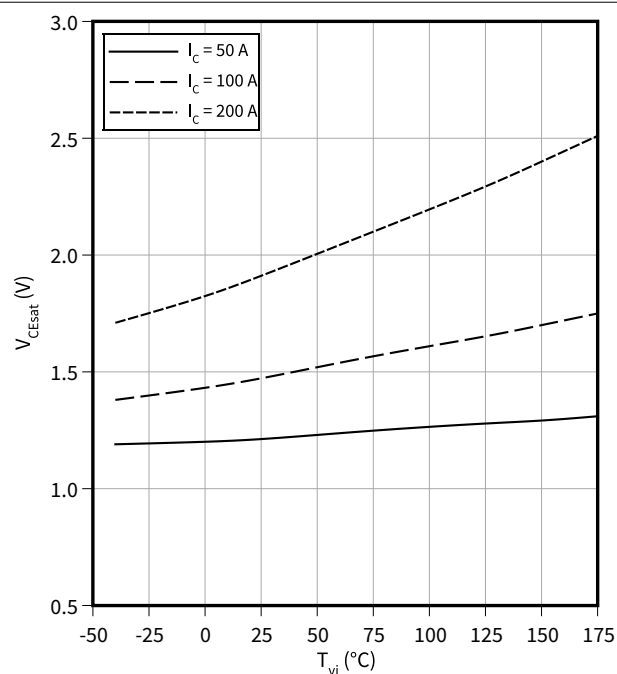
$$V_{CE} = 20 \text{ V}$$



## Typical collector-emitter saturation voltage as a function of junction temperature

$$V_{CEsat} = f(T_{vj})$$

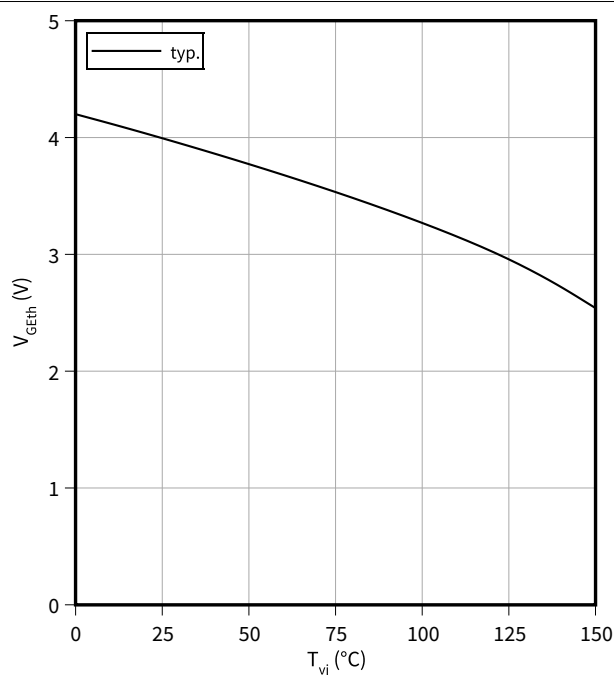
$$V_{GE} = 15 \text{ V}$$



## Gate-emitter threshold voltage as a function of junction temperature

$$V_{GEth} = f(T_{vj})$$

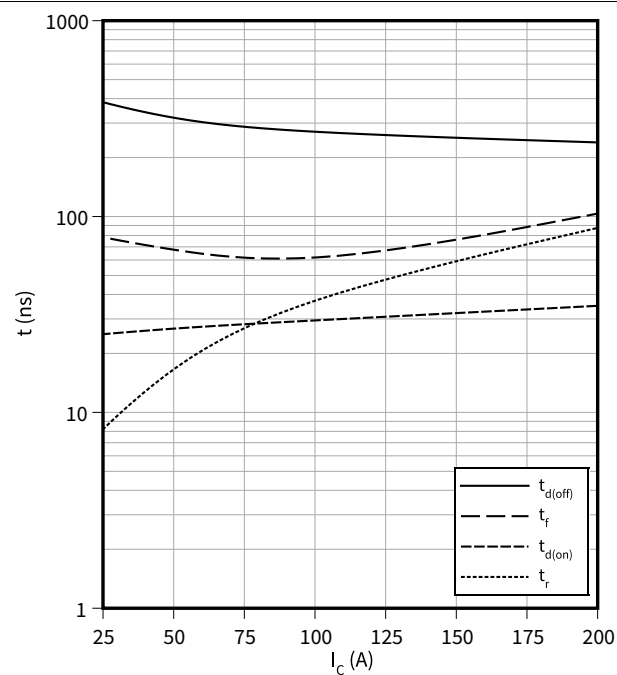
$$I_C = 0.88 \text{ mA}$$



## Typical switching times as a function of collector current

$$t = f(I_C)$$

$$V_{GE} = 0/15 \text{ V}, R_G = 10 \Omega, V_{CC} = 400 \text{ V}, T_{vj} = 175^\circ\text{C}$$

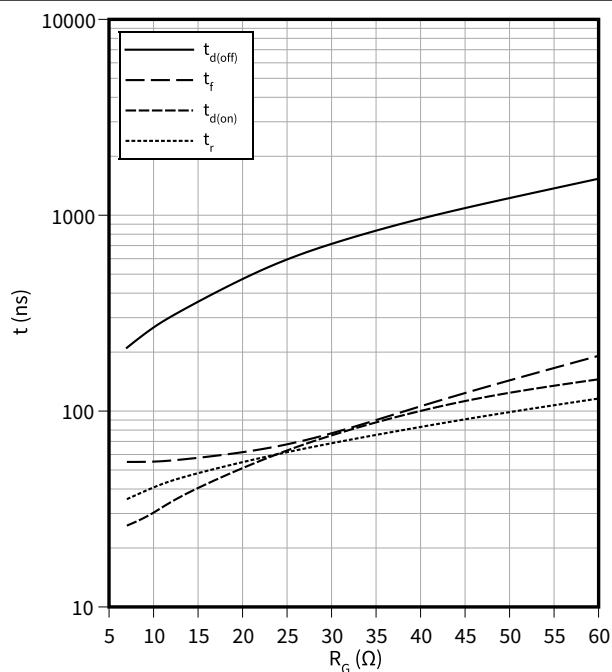




## 4 Characteristics diagrams

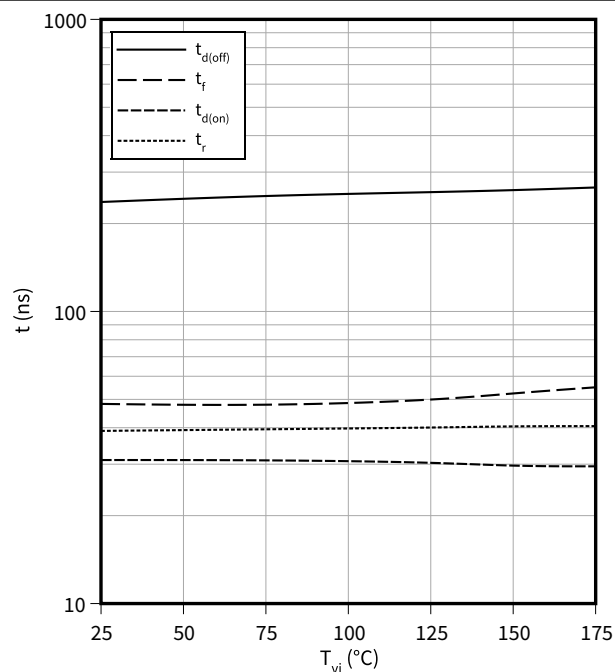
## Typical switching times as a function of gate resistor

$$t = f(R_G)$$

 $I_C = 100 \text{ A}, V_{CC} = 400 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = 0/15 \text{ V}$ 


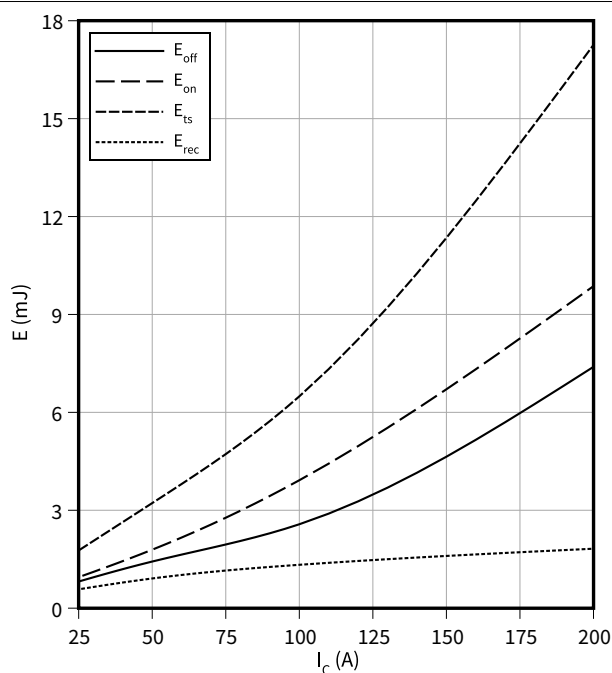
## Typical switching times as a function of junction temperature

$$t = f(T_{vj})$$

 $I_C = 100 \text{ A}, V_{CC} = 400 \text{ V}, V_{GE} = 0/15 \text{ V}, R_G = 10 \text{ } \Omega$ 


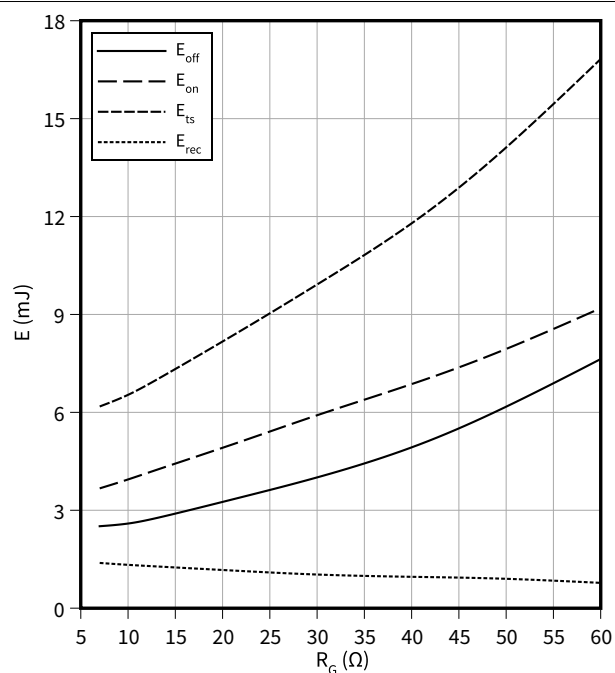
## Typical switching energy losses as a function of collector current

$$E = f(I_C)$$

 $V_{CC} = 400 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = 0/15 \text{ V}, R_G = 10 \text{ } \Omega$ 


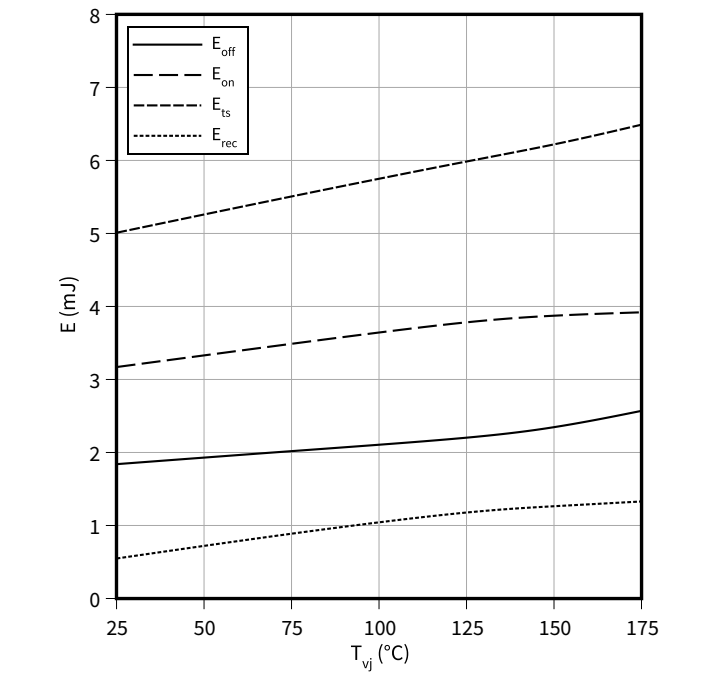
## Typical switching energy losses as a function of gate resistor

$$E = f(R_G)$$

 $I_C = 100 \text{ A}, V_{CC} = 400 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}, V_{GE} = 0/15 \text{ V}$ 


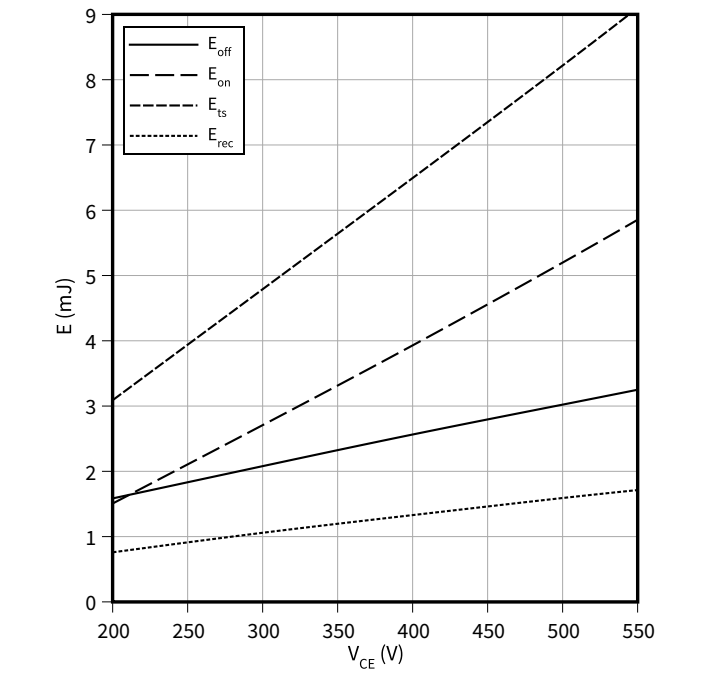
Typical switching energy losses as a function of junction temperature

$E = f(T_{vj})$   
 $I_C = 100\text{ A}$ ,  $V_{CC} = 400\text{ V}$ ,  $V_{GE} = 0/15\text{ V}$ ,  $R_G = 10\text{ }\Omega$



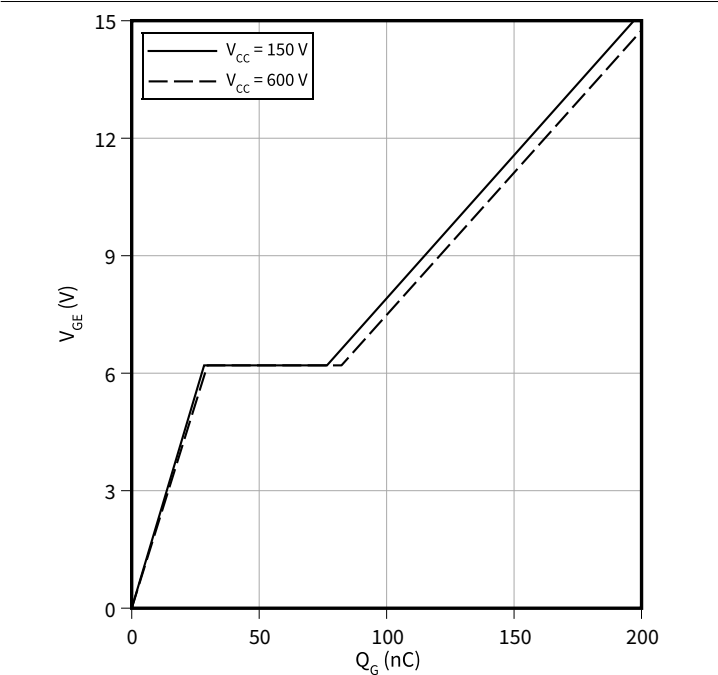
Typical switching energy losses as a function of collector emitter voltage

$E = f(V_{CE})$   
 $I_C = 100\text{ A}$ ,  $T_{vj} = 175\text{ }^\circ\text{C}$ ,  $V_{GE} = 0/15\text{ V}$ ,  $R_G = 10\text{ }\Omega$



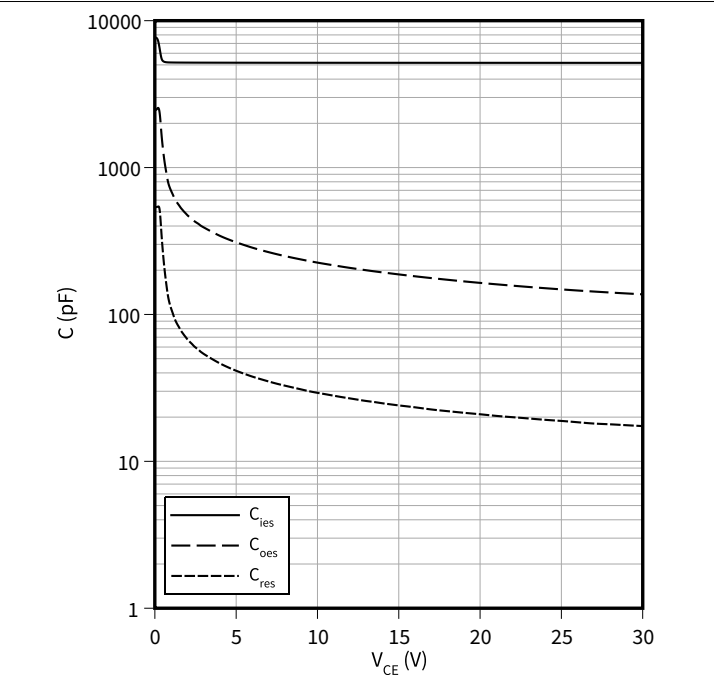
Typical gate charge

$V_{GE} = f(Q_G)$   
 $I_C = 100\text{ A}$



Typical capacitance as a function of collector-emitter voltage

$C = f(V_{CE})$   
 $f = 100\text{ kHz}$ ,  $V_{GE} = 0\text{ V}$

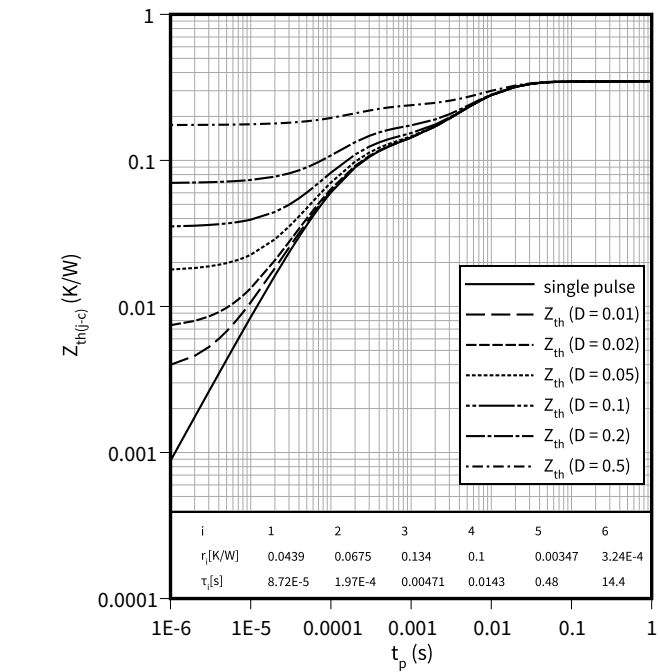


4 Characteristics diagrams

IGBT transient thermal impedance as a function of pulse width

$$Z_{th(j-c)} = f(t_p)$$

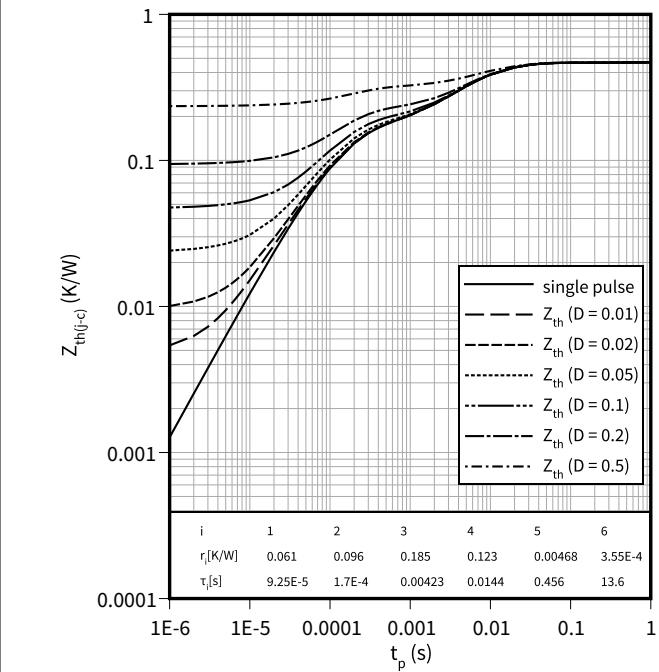
$$D = t_p/T$$



Diode transient thermal impedance as a function of pulse width

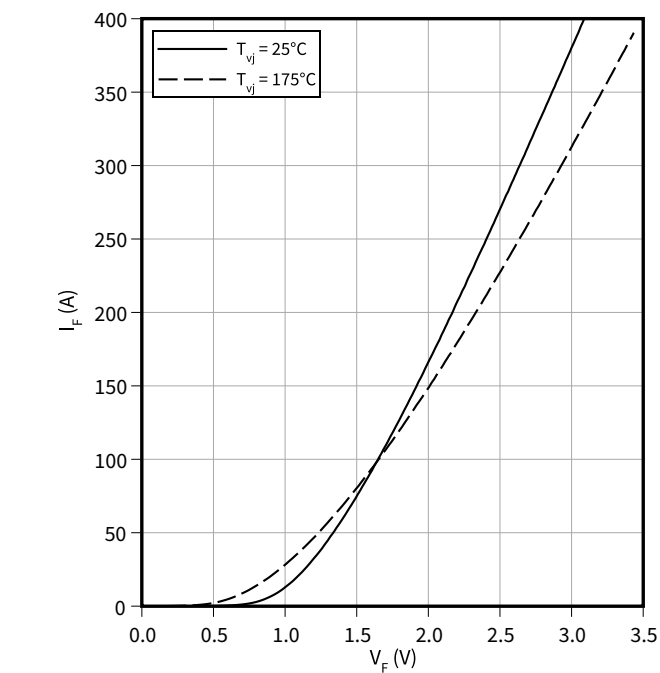
$$Z_{th(j-c)} = f(t_p)$$

$$D = t_p/T$$



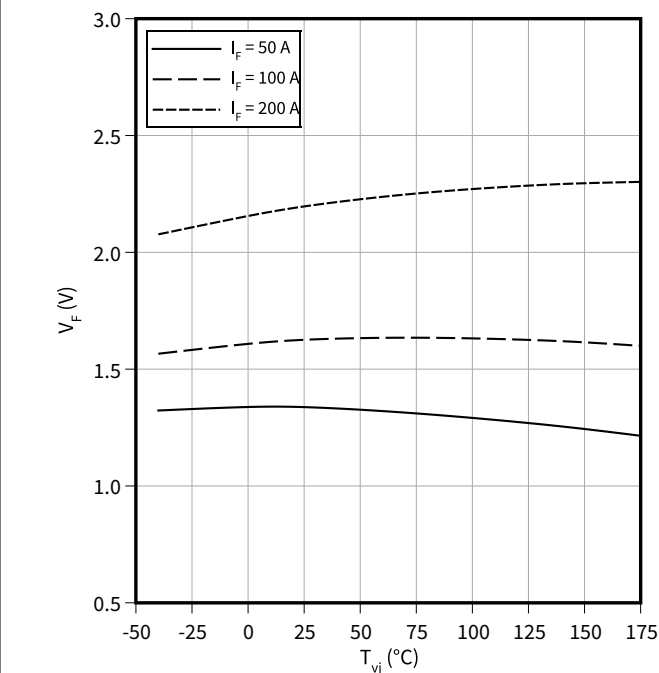
Typical diode forward current as a function of forward voltage

$$I_F = f(V_F)$$



Typical diode forward voltage as a function of junction temperature

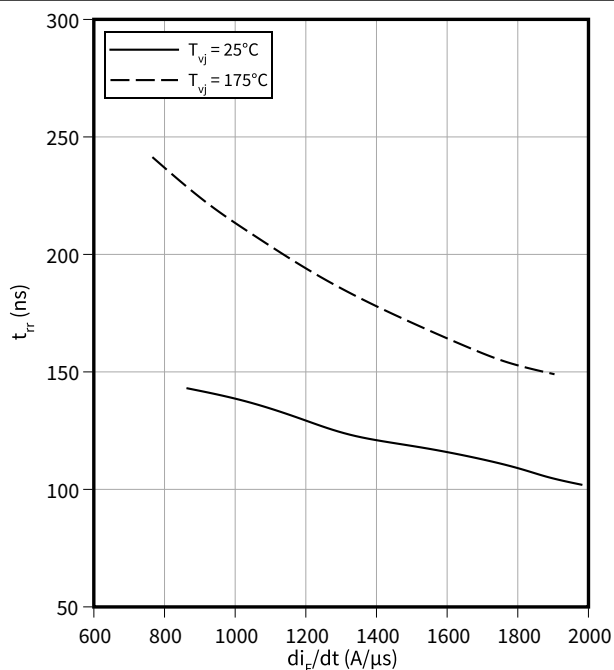
$$V_F = f(T_{vj})$$



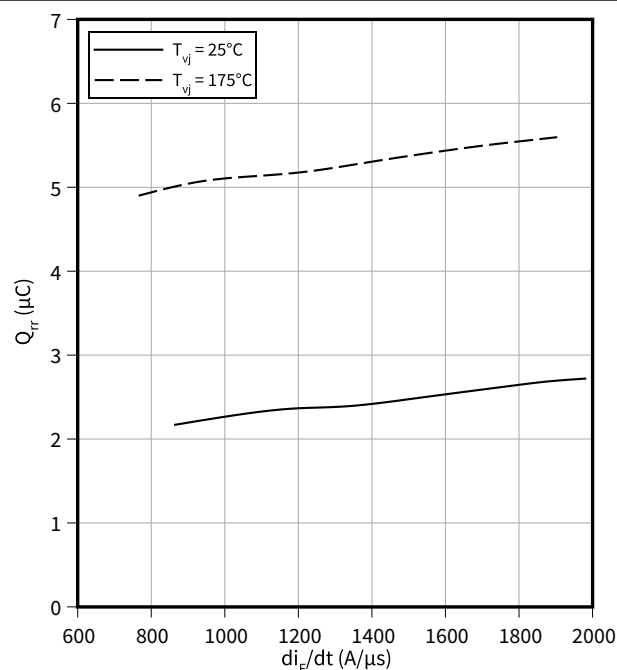
## 4 Characteristics diagrams

**Typical reverse recovery time as a function of diode current slope**

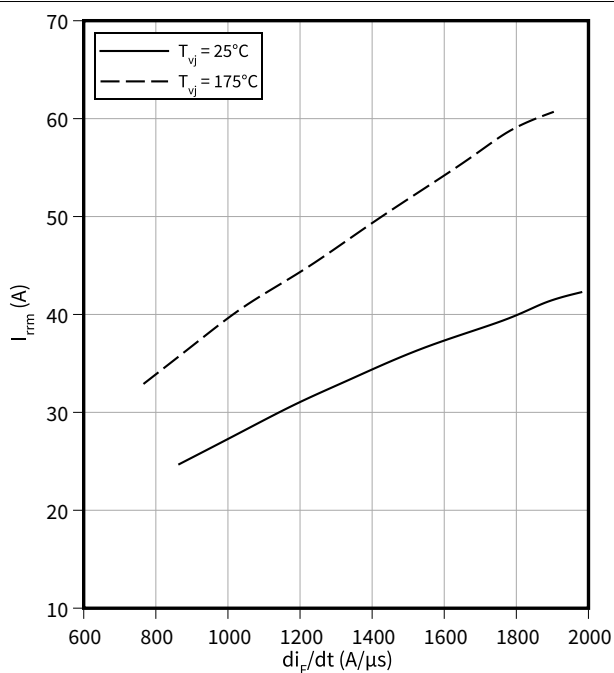
$$t_{rr} = f(di_F/dt)$$

 $V_R = 400 \text{ V}, I_F = 100 \text{ A}$ 
**Typical reverse recovery charge as a function of diode current slope**

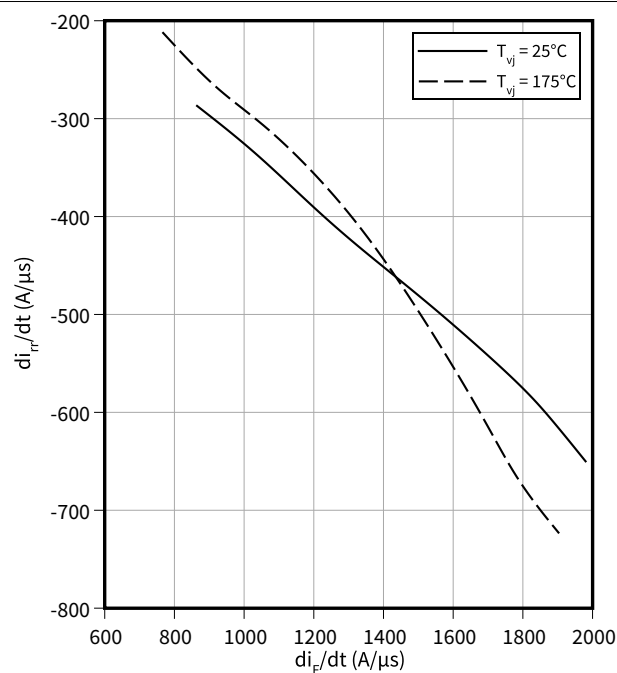
$$Q_{rr} = f(di_F/dt)$$

 $V_R = 400 \text{ V}, I_F = 100 \text{ A}$ 
**Typical reverse recovery current as a function of diode current slope**

$$I_{rrm} = f(di_F/dt)$$

 $V_R = 400 \text{ V}, I_F = 100 \text{ A}$ 
**Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**

$$di_{rr}/dt = f(di_F/dt)$$

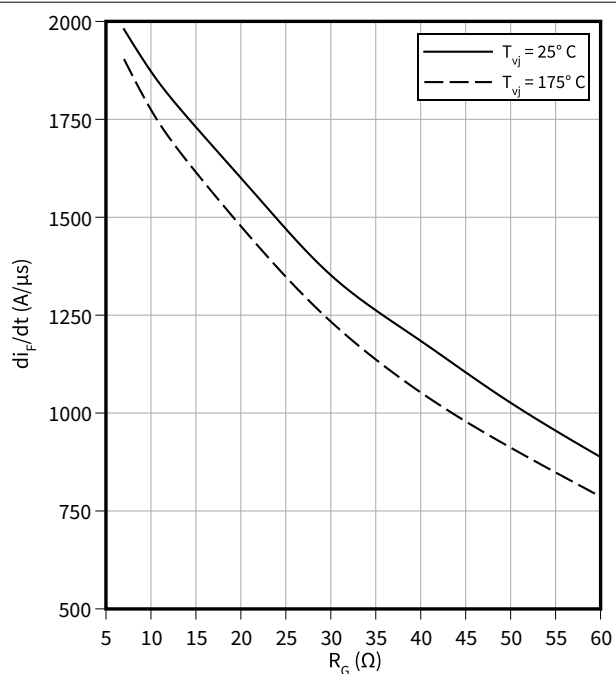
 $V_R = 400 \text{ V}, I_F = 100 \text{ A}$ 


## 4 Characteristics diagrams

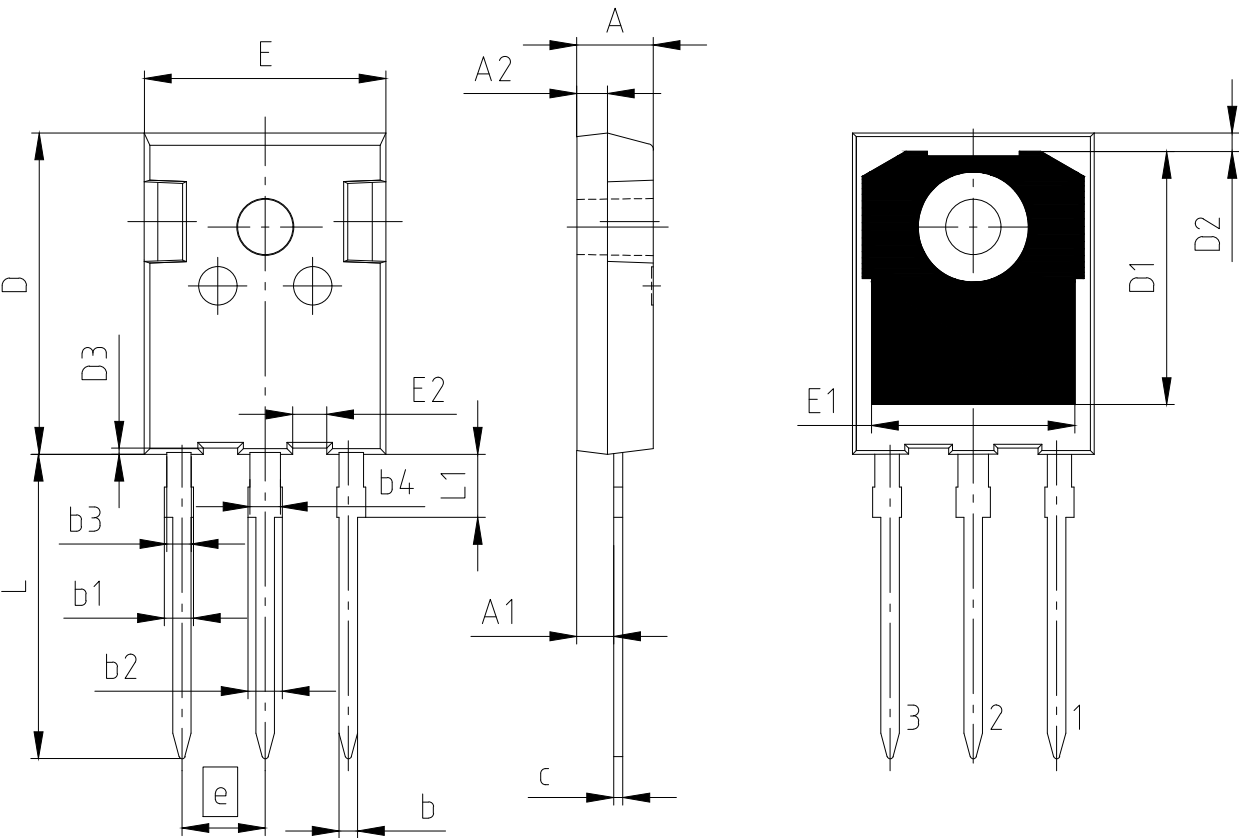
**Typical diode current slope as a function of gate resistor**

$$di_F/dt = f(R_G)$$

$$V_R = 400 \text{ V}, I_F = 100 \text{ A}$$



5 Package outlines



| PACKAGE - GROUP<br>NUMBER: <b>PG-TO247-3-U04</b> |             |       |
|--------------------------------------------------|-------------|-------|
| DIMENSIONS                                       | MILLIMETERS |       |
|                                                  | MIN.        | MAX.  |
| <b>A</b>                                         | 4.90        | 5.10  |
| <b>A1</b>                                        | 2.31        | 2.51  |
| <b>A2</b>                                        | 1.90        | 2.10  |
| <b>b</b>                                         | 1.16        | 1.26  |
| <b>b1</b>                                        |             | 1.90  |
| <b>b2</b>                                        |             | 2.30  |
| <b>b3</b>                                        | 1.55        | 1.65  |
| <b>b4</b>                                        | 1.96        | 2.06  |
| <b>c</b>                                         | 0.59        | 0.66  |
| <b>D</b>                                         | 20.90       | 21.10 |
| <b>D1</b>                                        | 16.25       | 16.85 |
| <b>D2</b>                                        | 1.05        | 1.35  |
| <b>D3</b>                                        | 0.55        | 0.65  |
| <b>E</b>                                         | 15.70       | 15.90 |
| <b>E1</b>                                        | 13.10       | 13.50 |
| <b>E2</b>                                        | 2.14        | 2.34  |
| <b>e</b>                                         | 5.44        |       |
| <b>N</b>                                         | 3           |       |
| <b>L</b>                                         | 19.80       | 20.10 |
| <b>L1</b>                                        | 3.95        | 4.30  |

Figure 1

## 6 Testing conditions

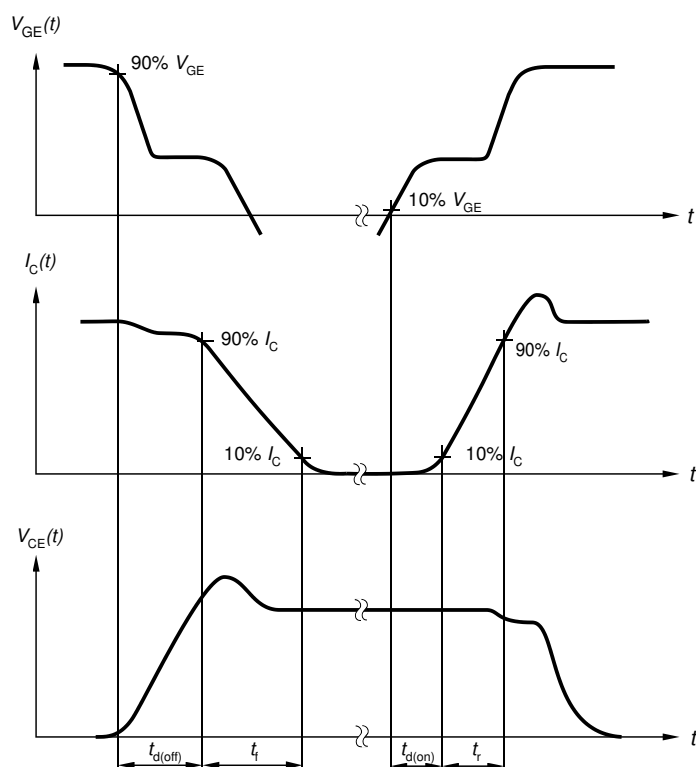


Figure A. Definition of switching times

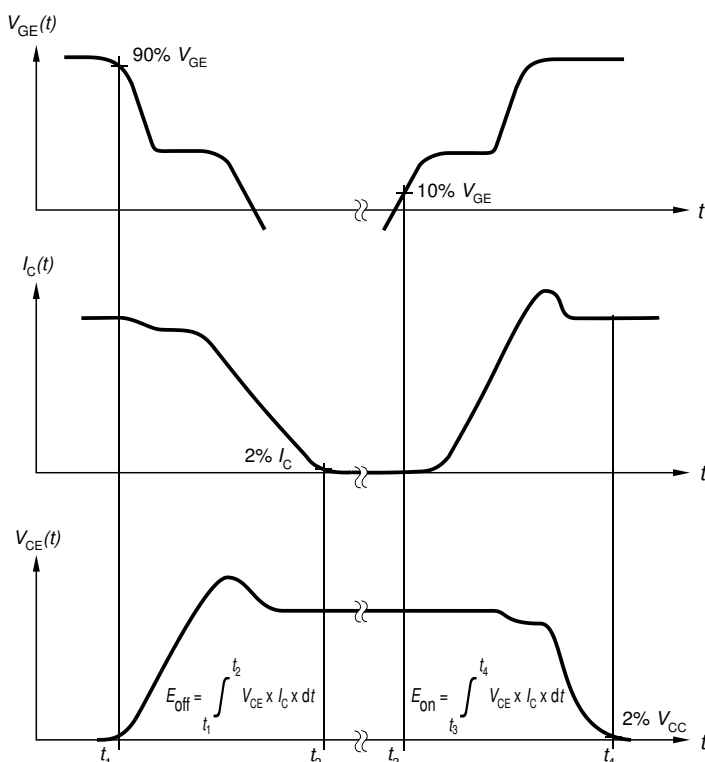


Figure B. Definition of switching losses

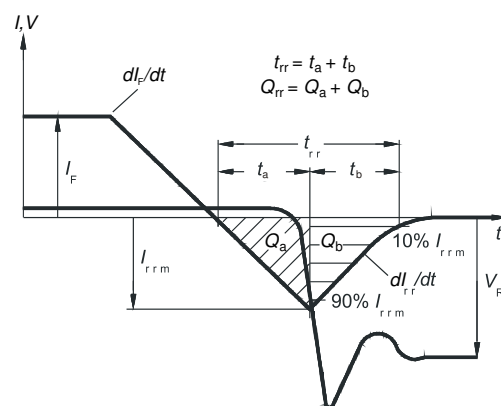


Figure C. Definition of diode switching characteristics

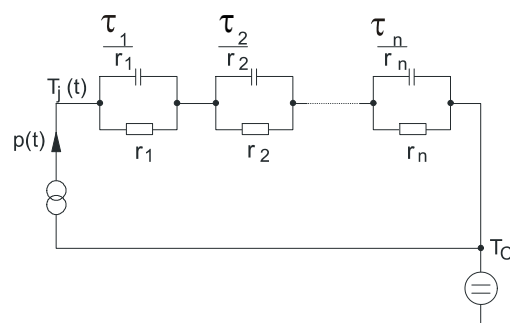


Figure D. Thermal equivalent circuit

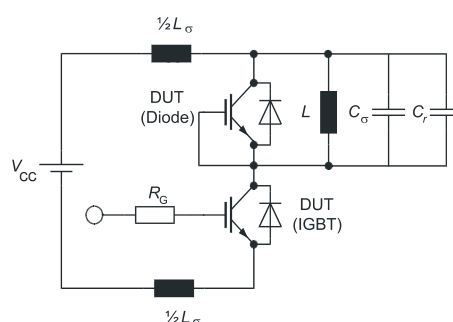


Figure E. Dynamic test circuit  
Parasitic inductance  $L_{\sigma}$ ,  
parasitic capacitor  $C_{\sigma}$ ,  
relief capacitor  $C_r$ ,  
(only for ZVT switching)

**Revision history**

| Document revision | Date of release | Description of changes |
|-------------------|-----------------|------------------------|
| 0.10              | 2025-03-20      | Preliminary datasheet  |
| 1.00              | 2025-07-31      | Final datasheet        |



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